



Future Normal in Semiconductor

2025-02-13(목), 09:00-10:45

좌장: 추후업데이트 예정

E. Compound Semiconductors 분과

[FL1-E] III-V Semiconductor

초청 FL1-E-1 09:00-09:30	고유민 (초청연사)
FL1-E-2 09:30-09:45	$L_g=50$ nm $\text{In}_{0.65}\text{Ga}_{0.35}\text{As}$ HEMTs with record noise-figure performance Min-Seo Yu ¹ , Seung-Woo Son ¹ , Sang-Ki Yun ¹ , Sang-Pyeong Son ¹ , Ji-Hoon Yoo ¹ , Kyounghoon Yang ² , Jae-Hak Lee ¹ , and Dae-Hyun Kim ¹ ¹ School of Electronic and Electrical Engineering, Kyungpook National University, ² KAIST
FL1-E-3 09:45-10:00	M3D InGaAs MOSHEMT on Si Substrate with Low Gate Leakage Current Yoon-Je Suh, Jaeyong Jeong, Nahyun Rheem, Chan Jik Lee, and Sanghyeon Kim KAIST
FL1-E-4 10:00-10:15	$L_g = 50$ nm gate-all-around $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ nanosheet MOSFETs J.-H. Yoo ¹ , H.-B. Jo ^{1,2} , I.-G. Lee ¹ , S.-M. Choi ¹ , H.-J. Kim ¹ , W. -S. Park ¹ , H. Jang ³ , C.-S. Shin ³ , K.-S. Seo ³ , SK. Kim ⁴ , JG. Kim ⁴ , J. Yun ⁴ , T. Kim ⁴ , J.-H. Lee ¹ , and D.-H. Kim ¹ ¹ Kyungpook National University, ² KETI, ³ KANC, ⁴ QSI
FL1-E-5 10:15-10:30	Study of 1.65 eV $\text{Al}_{0.18}\text{Ga}_{0.82}\text{As}$ Tunnel Junction with Hybrid Delta-Doped n-GaAs Quantum Well for Monolithic III-V/Si Tandem Solar Cells Won Jun Choi ¹ , In-Hwan Lee ² , Eunkyo Ju ^{1,2} , Yeonhwa Kim ^{1,2} , May Angelu Madarang ^{1,3} , Rafael Jumar Chu ^{1,3} , Tsimafei Laryn ^{1,3} , and Daehwan Jung ^{1,3} ¹ Center for Quantum Technology, KIST, ² Department of Materials Science and Engineering, Korea University, ³ Division of Nanoscience and Technology, UST
FL1-E-6 10:30-10:45	Integration of InGaAs/InP Heterojunction Phototransistor on Si CMOS Platform by Wafer Bonding. Kyunghwan Kim, Dae-Hwan Ahn and Jae-Hoon Han Center for Quantum Technology, KIST